

PATENT

AMENDMENTS TO THE SPECIFICATION

Please amend the title in all instances as follows:

BIPOLAR TRANSISTOR WITH AN ULTRA SMALL SELF-ALIGNED POLYSILICON
EMITTER AND ~~METHOD OF FORMING THE SILICON GERMANIUM BASE OF THE~~
TRANSISTOR

Please amend the first paragraph on page 1 as follows:

*881
61305*
~~The present application~~ This is a divisional application of Application Serial No.
09/994,293 filed on November 26, 2002, ^{*2001 now patent 6,753,234*} ~~which~~ ^{*now patent 6,649,482*} is a continuation-in-part of
Application Serial No. 09/882,740 filed June 15, 2001, by Abdalla Aly Naem for
Bipolar Transistor with a Silicon Germanium Base and an Ultra Small Self-Aligned
Polysilicon Emitter and Method of Forming the Transistor.